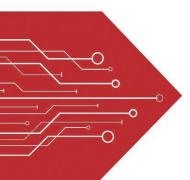
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Product data sheet

www.msksemi.com

Mechanical Characteristics

Package: SOD-323Lead Finish: Matte Tin

Case Material: "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
 Moisture Sensitivity: Level 3 per J-STD-020
 Terminal Connections: See Diagram Below

Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Peripherals
- Pagers Peripherals
- Desktop and Servers

Dimensions and Pin Configuration

SOD-323

Features

- 500W peak pulse power (8/20µs)
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage:3.3V, 5V, 12V,15, 24V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 Contact discharge: ±30kV
 IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	Ppk	500	W	
ESD per IEC 61000-4-2 (Air)	1/505	±30	14) /	
ESD per IEC 61000-4-2 (Contact)	VESD	±30	kV	
Operating Temperature Range	TJ	−55 to +125	°C	
Storage Temperature Range	Tstg	−55 to +150	°C	

Electrical Characteristics (T_A=25°C unless otherwise specified)

ESD3V3L1BA-MS							
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Reverse Working Voltage	VRWM			3.3	V		
Breakdown Voltage	VBR	4			V	IT = 1mA	
Reverse Leakage Current	I _R			0.5	μA	VRWM = 5V	
Clamping Voltage	Vc		5		V	IPP = 5A (8 x 20μs pulse)	
Clamping Voltage	Vc		10		V	IPP = 36A (8 x 20µs pulse)	
Peak Pulse Current	Ipp			18	Α	tp = 8/20µs	
Junction Capacitance	Сл			200	pF	VR = 0V, f = 1MHz	

ESD5V0L1BA-MS							
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Reverse Working Voltage	VRWM			5	V		
Breakdown Voltage	VBR	8.5			V	IT = 1mA	
Reverse Leakage Current	I _R			1	μA	VRWM = 8V	
Clamping Voltage	Vc			11	V	IPP = 5A (8 x 20µs pulse)	
Clamping Voltage	Vc			15	V	IPP = 34A (8 x 20µs pulse)	
Peak Pulse Current	Ipp			15	Α	tp = 8/20µs	
Junction Capacitance	Cl			180	pF	VR = 0V, f = 1MHz	

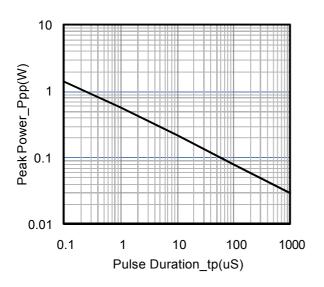
ESD12VL1BA-MS						
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 12V
Clamping Voltage	Vc			19	V	IPP = 5A (8 x 20µs pulse)
Clamping Voltage	Vc			28	V	IPP = 18A (8 x 20µs pulse)
Peak Pulse Current	Ipp			10	Α	tp = 8/20µs
Junction Capacitance	CJ			100	pF	VR = 0V, f = 1MHz

ESD15VL1BA-MS							
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Reverse Working Voltage	VRWM			15	V		
Breakdown Voltage	VBR	16.7			V	IT = 1mA	
Reverse Leakage Current	I _R			0.5	μΑ	VRWM = 12V	
Clamping Voltage	Vc			19	V	IPP = 5A (8 x 20µs pulse)	
Clamping Voltage	Vc			28	V	IPP = 18A (8 x 20µs pulse)	
Peak Pulse Current	Ipp			10	Α	tp = 8/20µs	
Junction Capacitance	CJ			100	pF	VR = 0V, f = 1MHz	

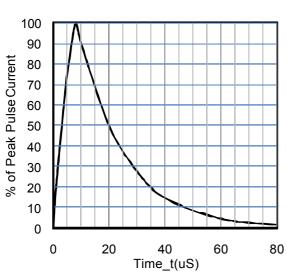


ESD24VL1BA-MS							
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Reverse Working Voltage	VRWM			24	V		
Breakdown Voltage	VBR	27			V	IT = 1mA	
Reverse Leakage Current	I _R			0.2	μA	VRWM = 24V	
Clamping Voltage	Vc			40	V	IPP = 1A (8 x 20μs pulse)	
Clamping Voltage	Vc			62	V	IPP = 8A (8 x 20μs pulse)	
Peak Pulse Current	Ipp			5	Α	tp = 8/20µs	
Junction Capacitance	CJ			50	pF	VR = 0V, f = 1MHz	

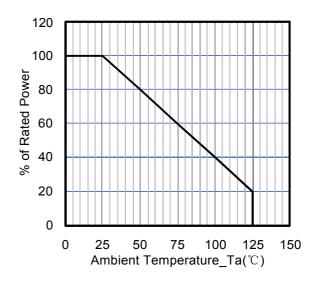
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



Peak Pulse Power vs. Pulse Time



8 X 20uS Pulse Waveform

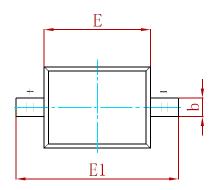


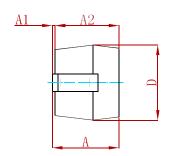
Power Derating Curve

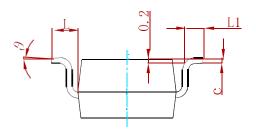




PACKAGE MECHANICAL DATA

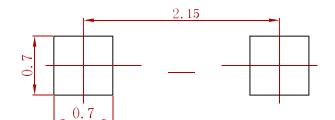






Cumb al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α		1.000		0.039	
A 1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
E	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L	0.47	REF.	0.019	REF.	
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
ESDXXXL1BA-MS	SOD-323	3000



Semiconductor

Compiance

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